



# STD150N3LLH6 STP150N3LLH6, STU150N3LLH6

N-channel 30 V, 0.0024  $\Omega$  , 80 A, DPAK, IPAK, TO-220  
STripFET™ VI DeepGATE™ Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STD150N3LLH6	30 V	0.0028 $\Omega$	80 A
STP150N3LLH6	30 V	0.0033 $\Omega$	80 A
STu150N3LLH6	30 V	0.0033 $\Omega$	80 A

- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- High avalanche ruggedness
- Low gate drive power losses

## Application

- Switching applications

## Description

This product utilizes the 6th generation of design rules of ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R<sub>DS(on)</sub> in all packages.

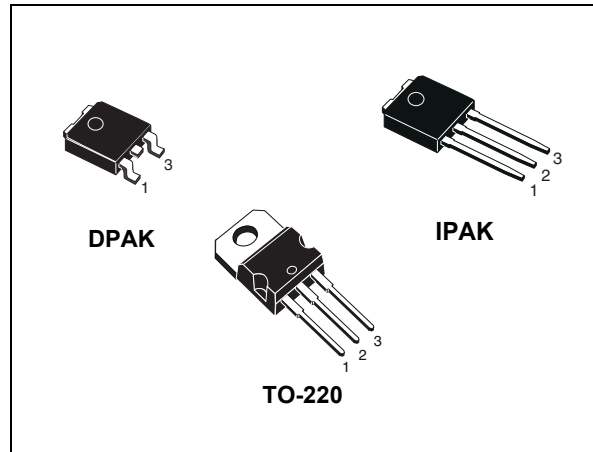


Figure 1. Internal schematic diagram

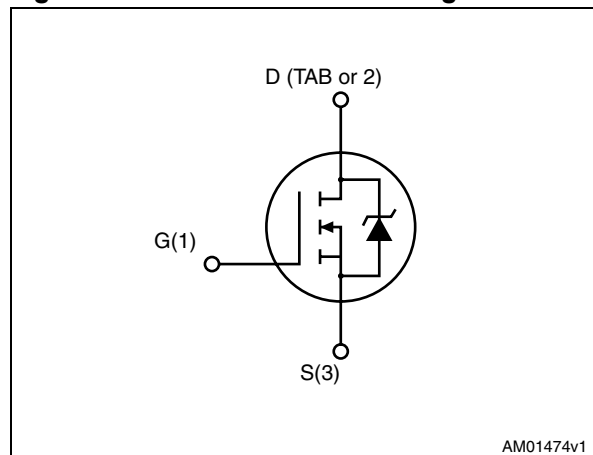


Table 1. Device summary

Order codes	Marking	Package	Packaging
STD150N3LLH6	150N3LLH6	DPAK	Tape and reel
STP150N3LLH6	150N3LLH6	TO-220	Tube
STU150N3LLH6	150N3LLH6	IPAK	Tube

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
	2.1 Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuit</b> .....	<b>8</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>14</b>
<b>6</b>	<b>Revision history</b> .....	<b>15</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
	Derating factor	0.73	W/°C
$E_{AS}^{(3)}$	Single pulse avalanche energy	525	mJ
$T_{stg}$	Storage temperature	-55 to 175	°C
$T_j$	Max. operating junction temperature	175	°C

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting  $T_j = 25\text{ }^\circ\text{C}$ ,  $I_D = 40\text{ A}$ ,  $V_{DD} = 25\text{ V}$

**Table 3. Thermal resistance**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.36	°C/W
$R_{thj-amb}$	Thermal resistance junction-case max	100	°C/W
$T_j$	Maximum lead temperature for soldering purpose	275	°C

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 30\text{ V}$ $V_{DS} = 30\text{ V}$ , $T_c = 125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$ SMD version		0.0024	0.0028	$\Omega$
		$V_{GS} = 10\text{ V}$ , $I_D = 40\text{ A}$		0.0029	0.0033	$\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 40\text{ A}$ SMD version		0.0034	0.0045	$\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 40\text{ A}$		0.0039	0.0049	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	4040	-	pF
$C_{oss}$	Output capacitance			740		pF
$C_{rss}$	Reverse transfer capacitance			425		pF
$Q_g$	Total gate charge	$V_{DD} = 15\text{ V}$ , $I_D = 80\text{ A}$	-	40	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 4.5\text{ V}$		16.3		nC
$Q_{gd}$	Gate-drain charge	(see Figure 14)		15.8		nC
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ gate bias Bias = 0 test signal level = 20 mV open drain	-	1.4	-	$\Omega$

**Table 6. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 15\text{ V}$ , $I_D = 40\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ <i>(see Figure 15)</i>	-	17 18	-	ns ns
$t_{d(off)}$ $t_f$	Turn-off delay time Fall time	$V_{DD} = 15\text{ V}$ , $I_D = 40\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$ <i>(see Figure 15)</i>	-	75 46	-	ns ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$ , $V_{GS} = 0$	-		1.1	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 24\text{ V}$ <i>(see Figure 17)</i>	-	34 35 2.1		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

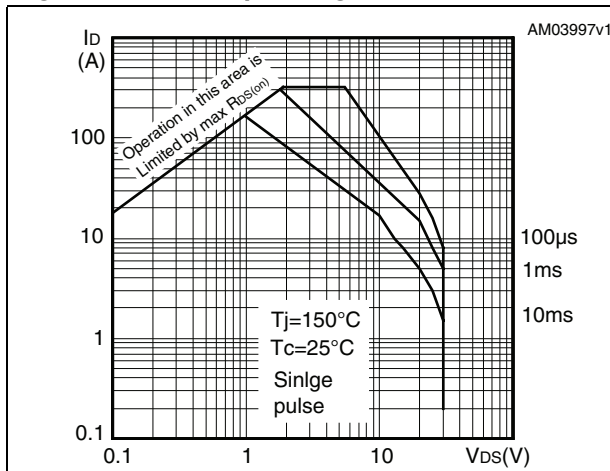


Figure 3. Thermal impedance

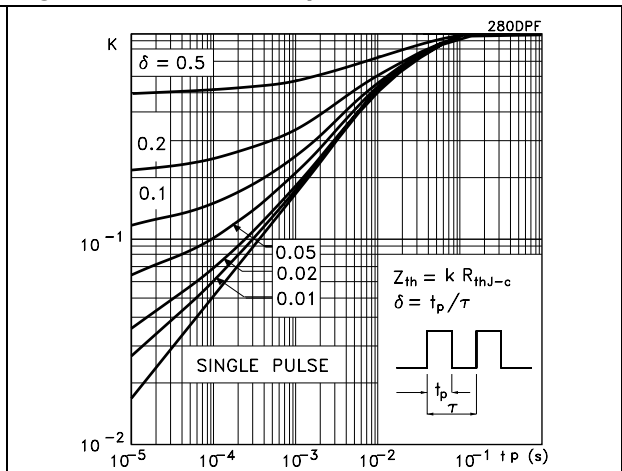


Figure 4. Output characteristics

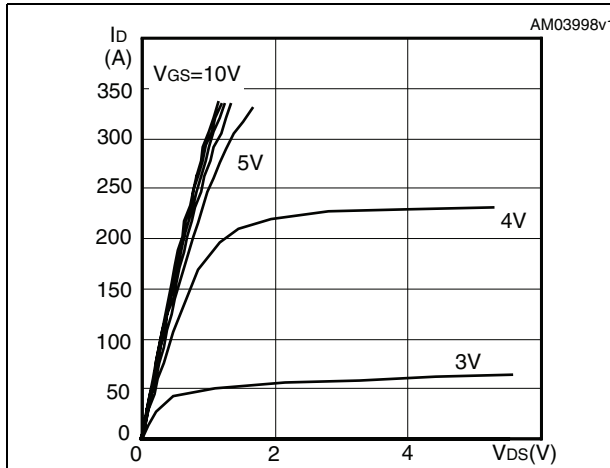


Figure 5. Transfer characteristics

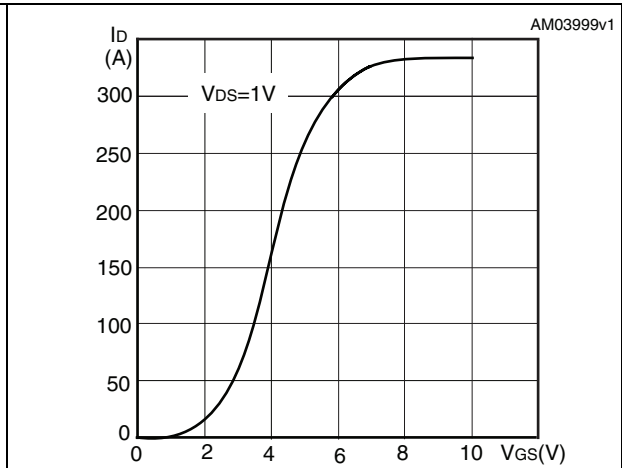


Figure 6. Normalized  $BV_{DSS}$  vs temperature

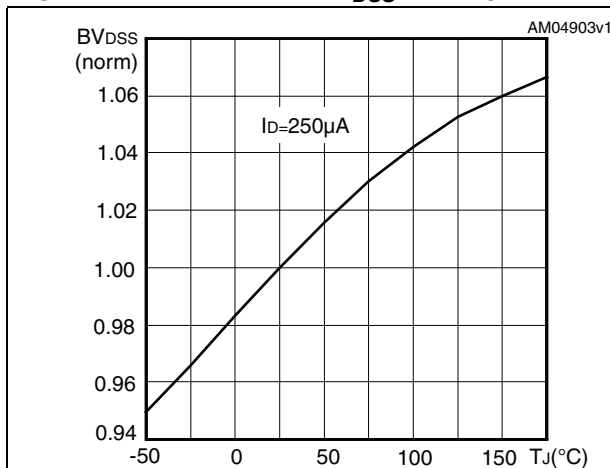


Figure 7. Static drain-source on resistance

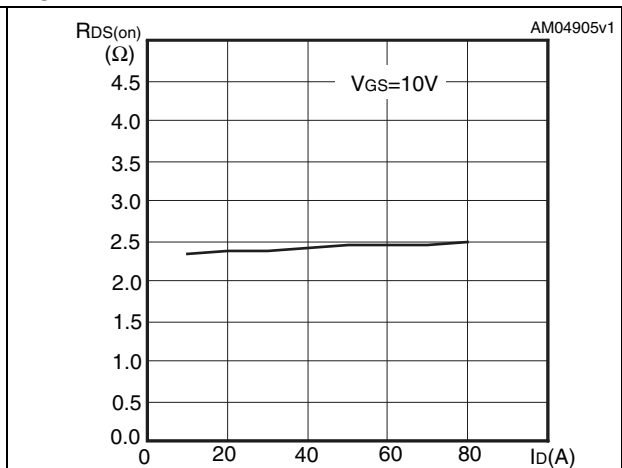


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

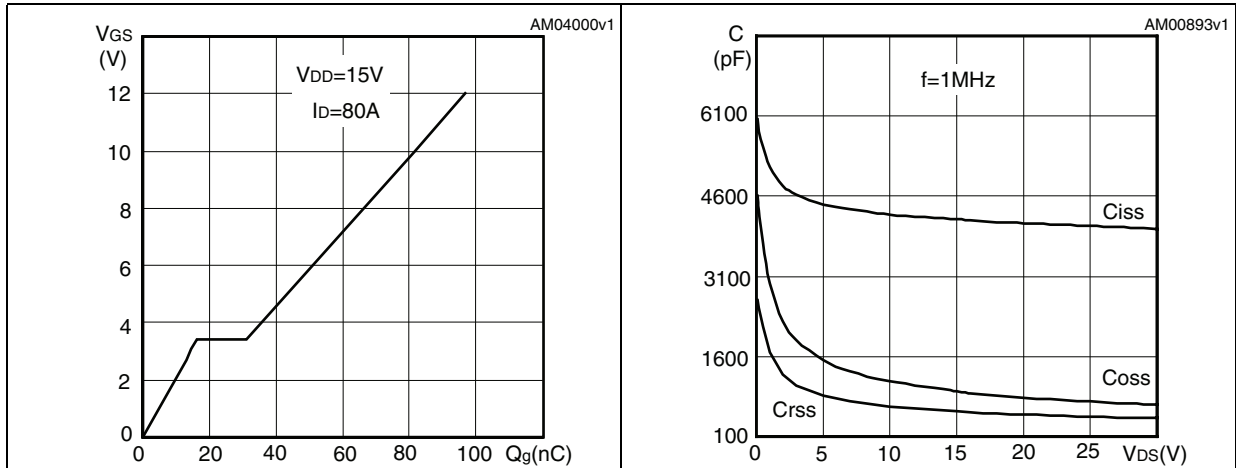


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

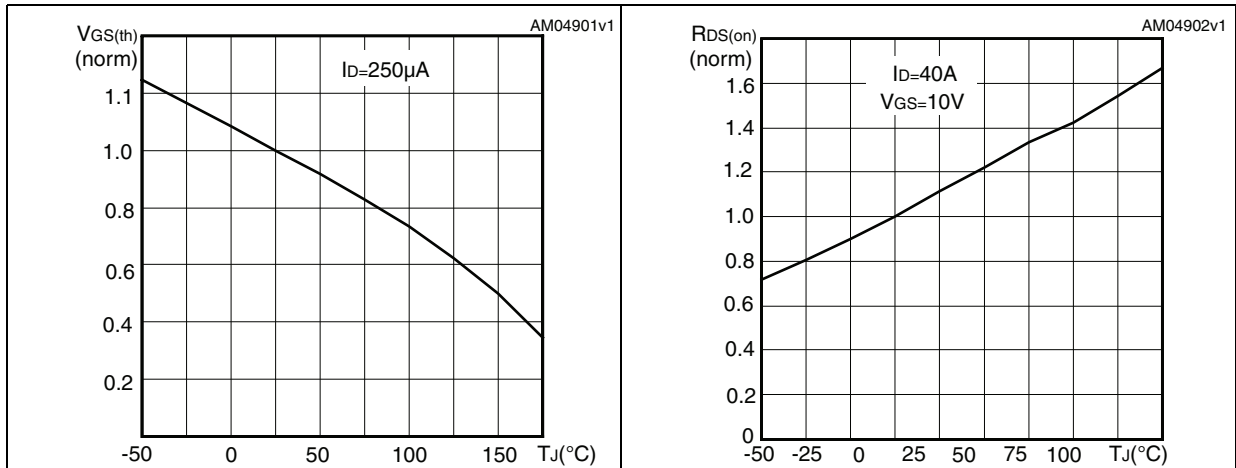
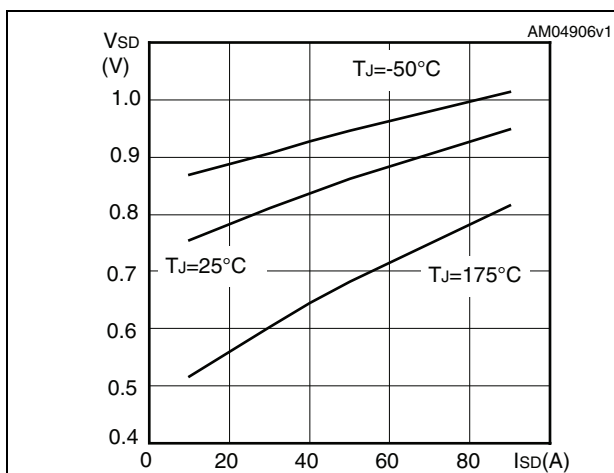
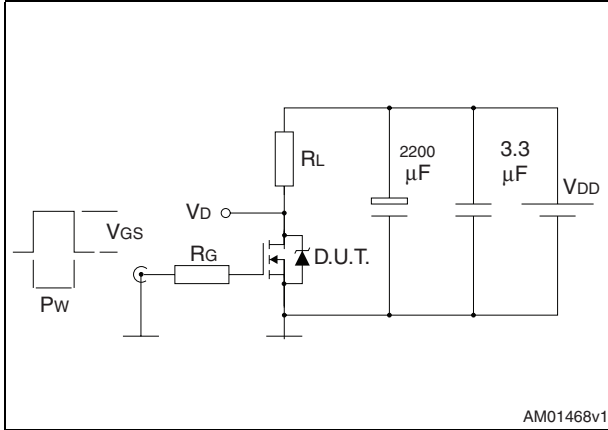


Figure 12. Source-drain diode forward characteristics

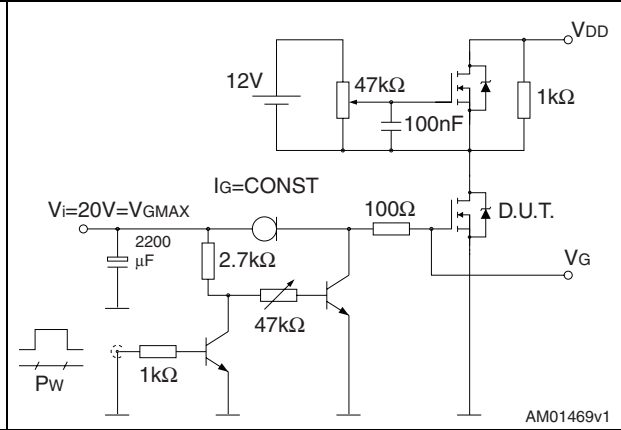


### 3 Test circuit

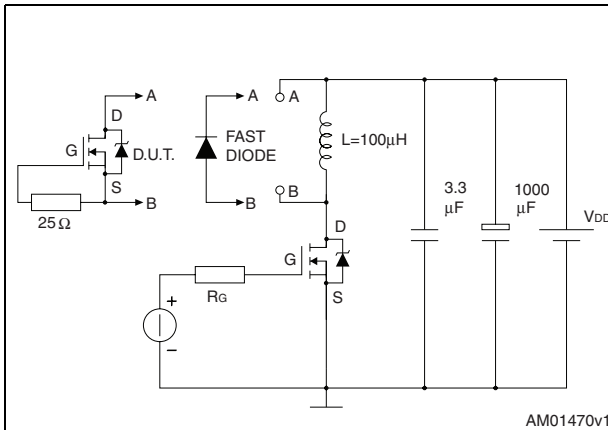
**Figure 13. Switching times test circuit for resistive load**



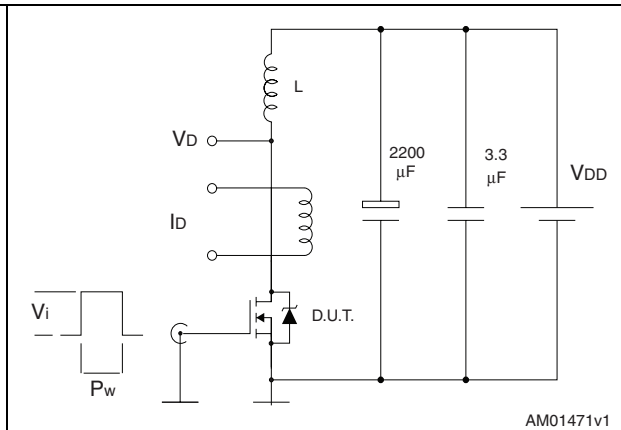
**Figure 14. Gate charge test circuit**



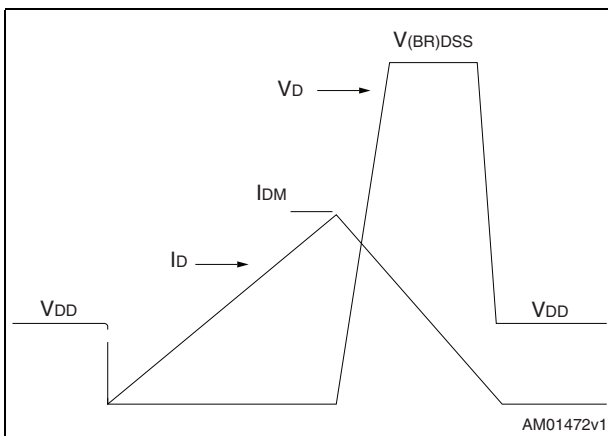
**Figure 15. Test circuit for inductive load switching and diode recovery times**



**Figure 16. Unclamped Inductive load test circuit**



**Figure 17. Unclamped inductive waveform**



**Figure 18. Switching time waveform**

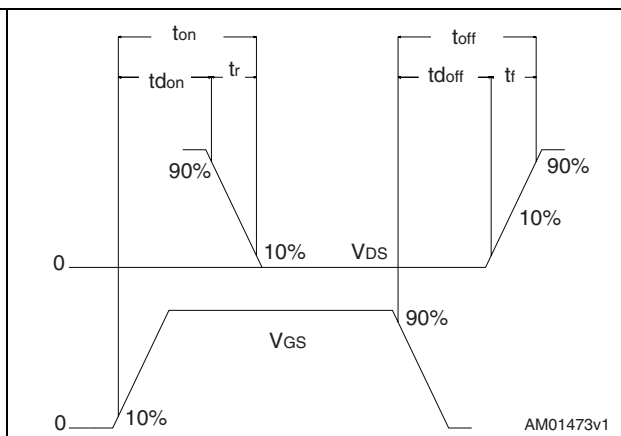
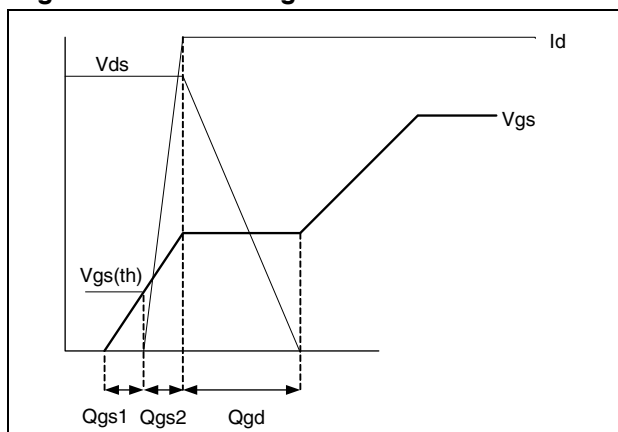




Figure 19. Gate charge waveform

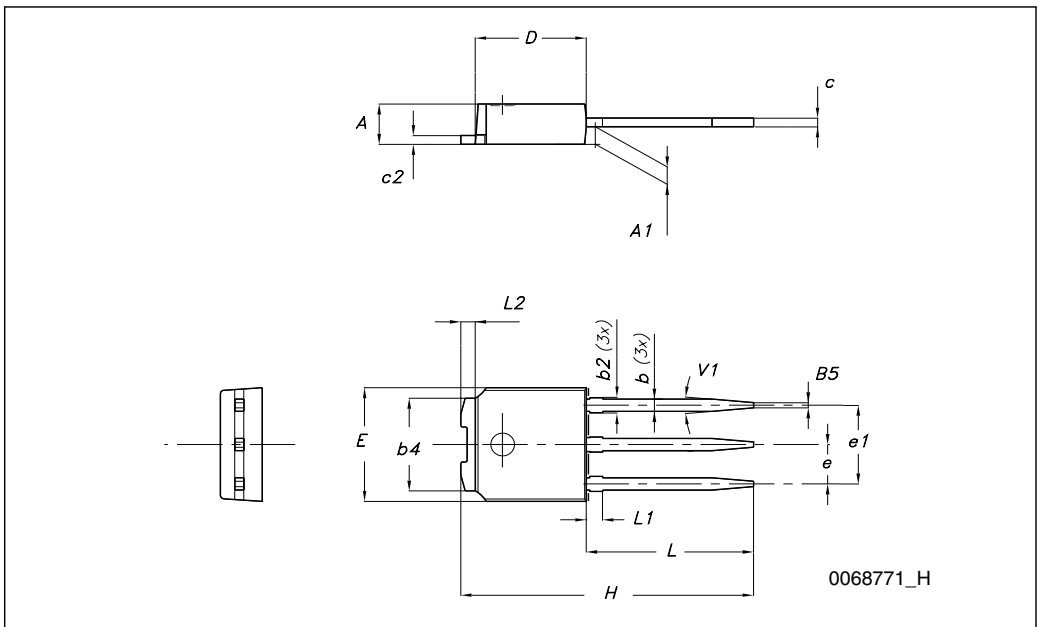


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

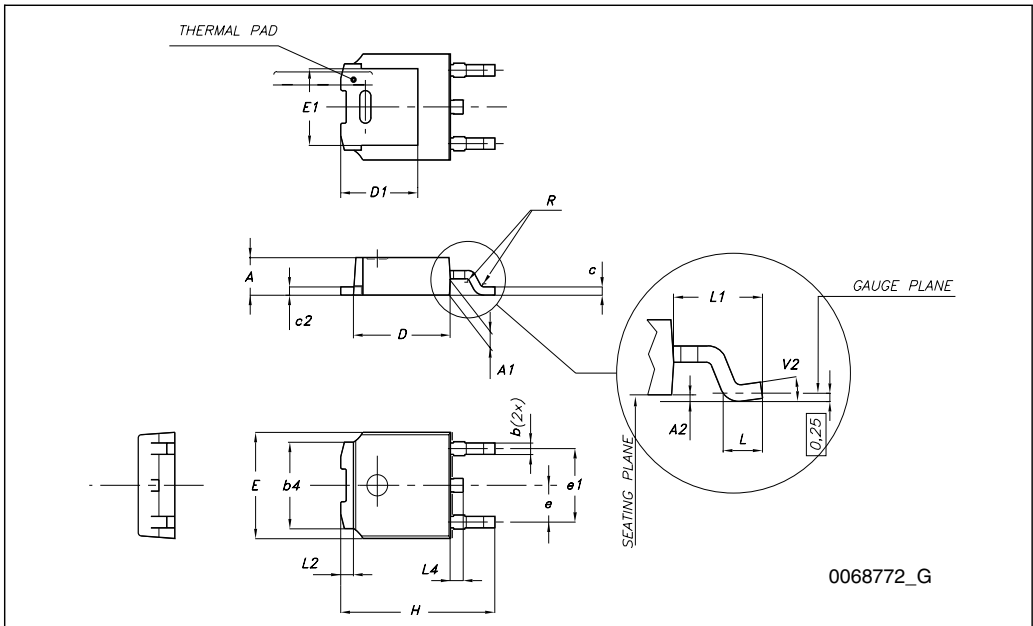
**TO-251 (IPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



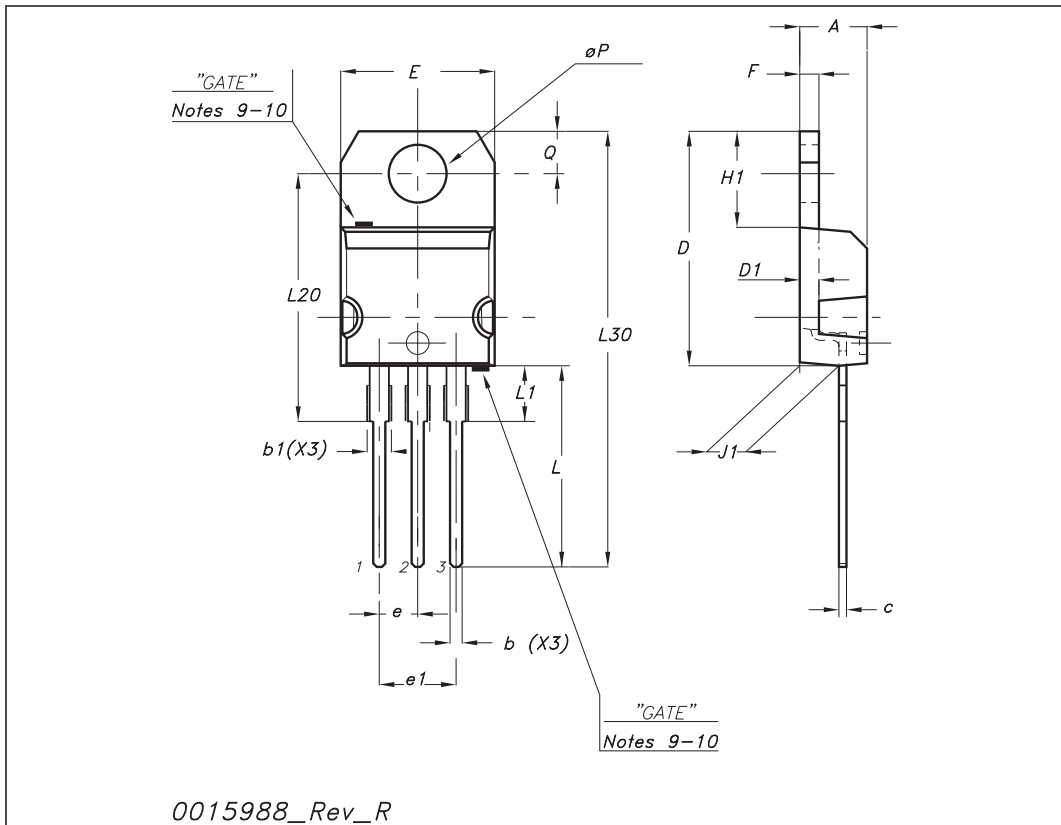
**TO-252 (DPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



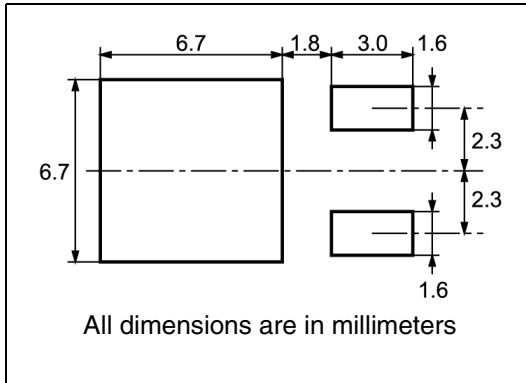
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



# 5 Packaging mechanical data

## DPAK FOOTPRINT



## TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

### REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

### TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

### BASE QTY

2500
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### BULK QTY

2500
------

For machine ref. only including draft and radii concentric around B0

10 pitches cumulative tolerance on tape +/- 0.2 mm

User Direction of Feed

FEED DIRECTION

Bending radius R min.

## 6 Revision history

**Table 8. Document revision history**

Date	Revision	Changes
01-Dec-2008	1	First release
20-Jul-2009	2	– Document status promoted from preliminary data to datasheet – Added new package, mechanical data: TO-220
10-Sep-2009	3	$Q_{gs}$ and $Q_{gd}$ values have been modified on <a href="#">Table 5: Dynamic</a>

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